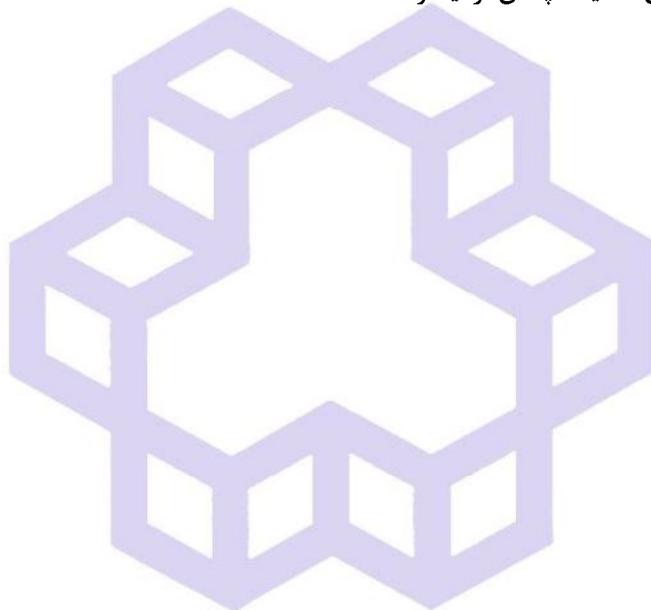


منابع

- ۱- کتاب تحلیل و طراحی مدارهای تکنیک پالس؛ مؤلف: دیوید بل ، مترجم: محمود دیانی.
- ۲- اصول و مبانی تکنیک پالس؛ مؤلف: دکتر سید احمد معتمدی.
- ۳- تکنیک پالس و مدارات دیجیتال؛ مؤلف: دکتر محمود تابنده.
- ۴- مدارهای میکروالکترونیک؛ مؤلف: عادل شفیق سدرة ، مترجم: محمود دیانی.
- ۵- جزوات تدریس شده در کلاس استاید محترم: دکتر حسین شمسی، دکتر حمید ابریشمی مقدم.
- ۶- فایلهای مرتبط با درس تکنیک پالس از اینترنت.





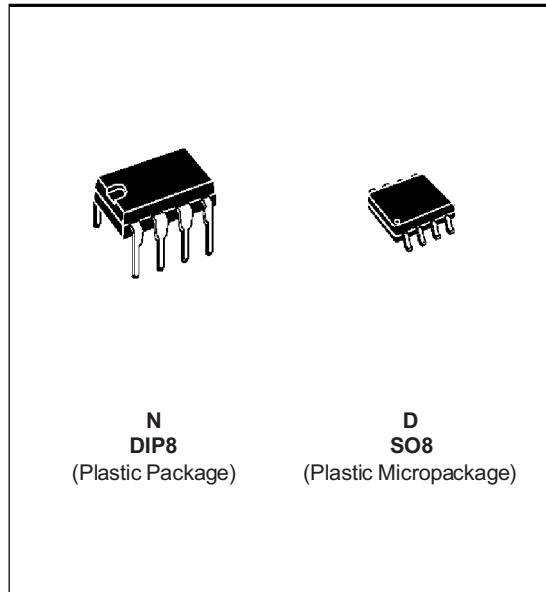
NE555 SA555 - SE555

GENERAL PURPOSE SINGLE BIPOLAR TIMERS

- LOW TURN OFF TIME
- MAXIMUM OPERATING FREQUENCY GREATER THAN 500kHz
- TIMING FROM MICROSECONDS TO HOURS
- OPERATES IN BOTH ASTABLE AND MONOSTABLE MODES
- HIGH OUTPUT CURRENT CAN SOURCE OR SINK 200mA
- ADJUSTABLE DUTY CYCLE
- TTL COMPATIBLE
- TEMPERATURE STABILITY OF 0.005% PER°C

DESCRIPTION

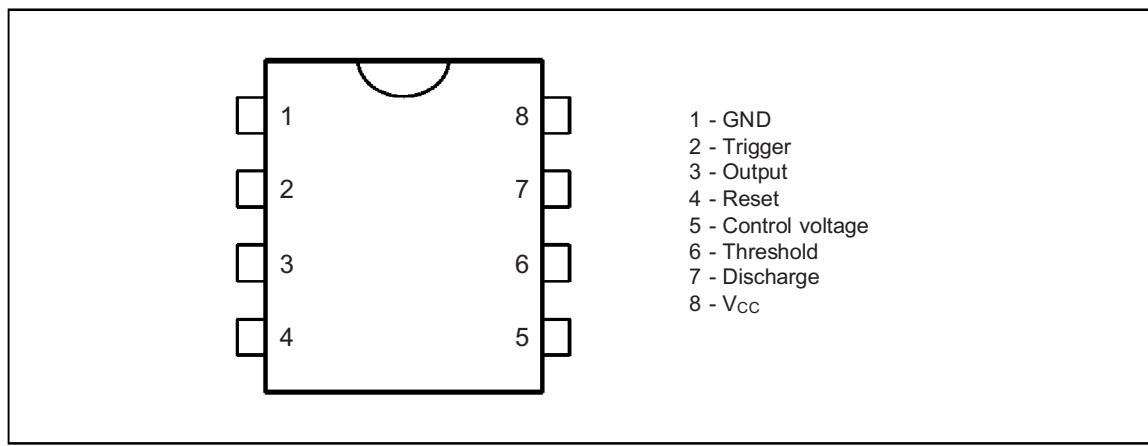
The NE555 monolithic timing circuit is a highly stable controller capable of producing accurate time delays or oscillation. In the time delay mode of operation, the time is precisely controlled by one external resistor and capacitor. For a stable operation as an oscillator, the free running frequency and the duty cycle are both accurately controlled with two external resistors and one capacitor. The circuit may be triggered and reset on falling waveforms, and the output structure can source or sink up to 200mA. The NE555 is available in plastic and ceramic minidip package and in a 8-lead micropackage and in metal can package version.



ORDER CODES

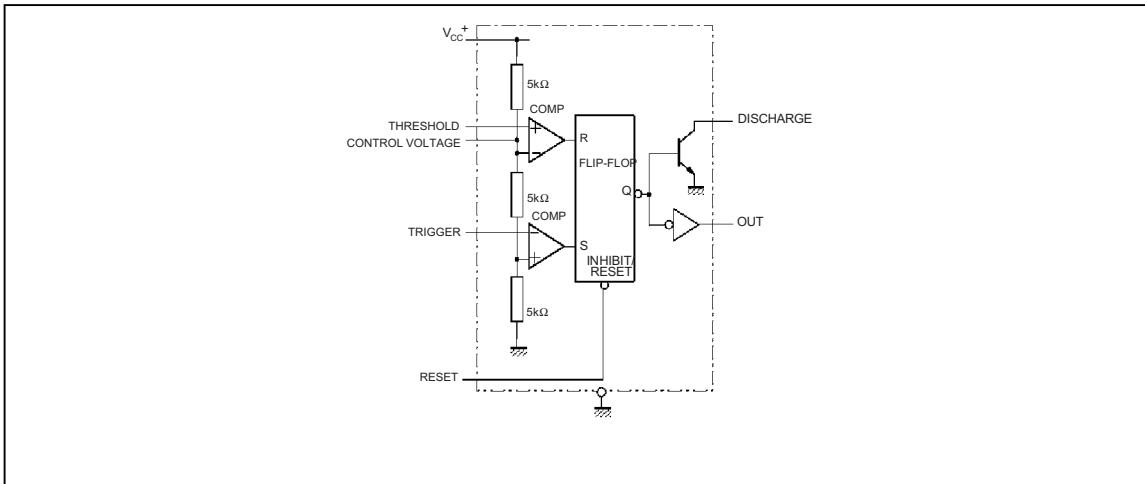
Part Number	Temperature Range		Package	
	N	D	N	D
NE555	0°C, 70°C		•	•
SA555	-40°C, 105°C		•	•
SE555	-55°C, 125°C		•	•

PIN CONNECTIONS (top view)

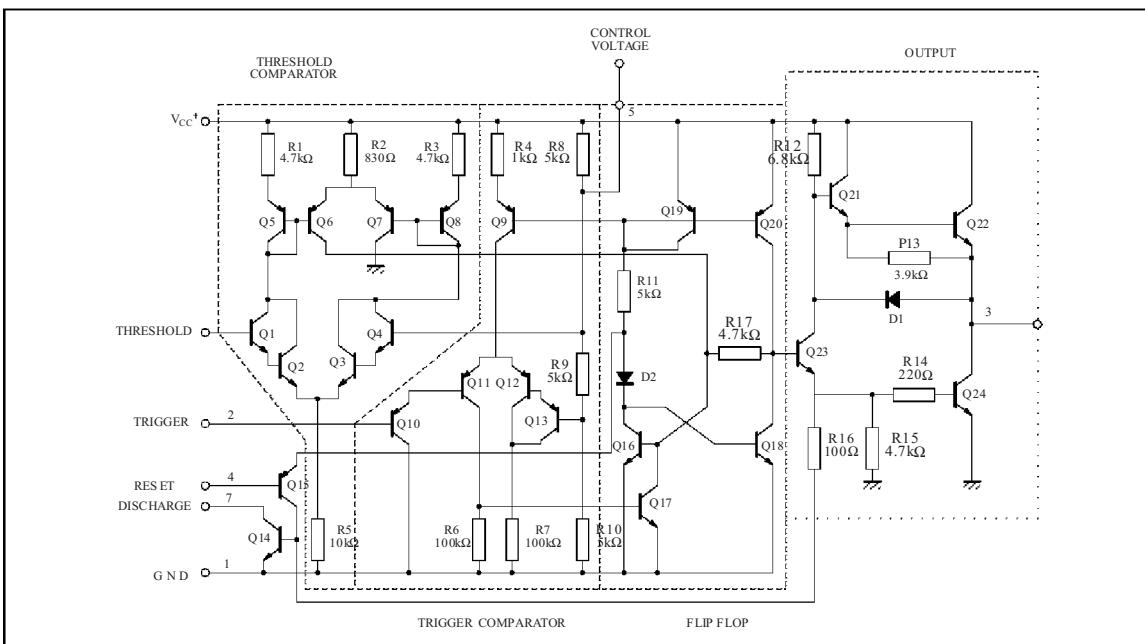


NE555/SA555/SE555

BLOCK DIAGRAM



SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	18	V
T_{oper}	Operating Free Air Temperature Range for NE555 for SA555 for SE555	0 to 70 -40 to 105 -55 to 125	°C
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-65 to 150	°C

OPERATING CONDITIONS

Symbol	Parameter	SE555	NE555 - SA555	Unit
V _{cc}	Supply Voltage	4.5 to 18	4.5 to 18	V
V _{th} , V _{trig} , V _{cl} , V _{reset}	Maximum Input Voltage	V _{cc}	V _{cc}	V

ELECTRICAL CHARACTERISTICS

T_{amb} = +25°C, V_{cc} = +5V to +15V (unless otherwise specified)

Symbol	Parameter	SE555			NE555 - SA555			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
I _{cc}	Supply Current (R _L ∞) (- note 1) Low State V _{cc} = +5V V _{cc} = +15V High State V _{cc} = 5V		3 10 2	5 12		3 10 2	6 15	mA
	Timing Error (monostable) (R _A = 2k to 100k Ω , C = 0.1 μ F) Initial Accuracy - (note 2) Drift with Temperature Drift with Supply Voltage		0.5 30 0.05	2 100 0.2		1 50 0.1	3 0.5	% ppm/ $^{\circ}$ C %/V
	Timing Error (astable) (R _A , R _B = 1k Ω to 100k Ω , C = 0.1 μ F, V _{cc} = +15V) Initial Accuracy - (note 2) Drift with Temperature Drift with Supply Voltage		1.5 90 0.15			2.25 150 0.3		% ppm/ $^{\circ}$ C %/V
V _{CL}	Control Voltage level V _{cc} = +15V V _{cc} = +5V	9.6 2.9	10 3.33	10.4 3.8	9 2.6	10 3.33	11 4	V
V _{th}	Threshold Voltage V _{cc} = +15V V _{cc} = +5V	9.4 2.7	10 3.33	10.6 4	8.8 2.4	10 3.33	11.2 4.2	V
I _{th}	Threshold Current - (note 3)		0.1	0.25		0.1	0.25	μ A
V _{trig}	Trigger Voltage V _{cc} = +15V V _{cc} = +5V	4.8 1.45	5 1.67	5.2 1.9	4.5 1.1	5 1.67	5.6 2.2	V
I _{trig}	Trigger Current (V _{trig} = 0V)		0.5	0.9		0.5	2.0	μ A
V _{reset}	Reset Voltage - (note 4)	0.4	0.7	1	0.4	0.7	1	V
I _{reset}	Reset Current V _{reset} = +0.4V V _{reset} = 0V		0.1 0.4	0.4 1		0.1 0.4	0.4 1.5	mA
V _{OL}	Low Level Output Voltage V _{cc} = +15V, I _{O(sink)} = 10mA I _{O(sink)} = 50mA I _{O(sink)} = 100mA I _{O(sink)} = 200mA V _{cc} = +5V, I _{O(sink)} = 8mA I _{O(sink)} = 5mA		0.1 0.4 2 2.5 0.05	0.15 0.5 2.2 2.5 0.2		0.1 0.4 2 2.5 0.3 0.25	0.25 0.75 2.5 0.4 0.35	V
V _{OH}	High Level Output Voltage V _{cc} = +15V, I _{O(source)} = 200mA I _{O(source)} = 100mA V _{cc} = +5V, I _{O(source)} = 100mA	13 3	12.5 13.3 3.3		12.75 2.75 3.3	12.5 13.3 3.3		V

- Notes :
1. Supply current when output is high is typically 1mA less.
 2. Tested at V_{cc} = +5V and V_{cc} = +15V.
 3. This will determine the maximum value of R_A + R_B for +15V operation the max total is R = 20M Ω and for 5V operation the max total R = 3.5M Ω .

NE555/SA555/SE555

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	SE555			NE555 - SA555			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
$I_{dis(off)}$	Discharge Pin Leakage Current (output high) ($V_{dis} = 10V$)		20	100		20	100	nA
$V_{dis(sat)}$	Discharge pin Saturation Voltage (output low) - (note 5) $V_{CC} = +15V, I_{dis} = 15mA$ $V_{CC} = +5V, I_{dis} = 4.5mA$		180 80	480 200		180 80	480 200	mV
t_r t_f	Output Rise Time Output Fall Time		100 100	200 200		100 100	300 300	ns
t_{off}	Turn off Time - (note 6) ($V_{reset} = V_{CC}$)		0.5			0.5		μs

Notes : 5. No protection against excessive Pin 7 current is necessary, providing the package dissipation rating will not be exceeded.
6. Time measured from a positive going input pulse from 0 to $0.8 \times V_{CC}$ into the threshold to the drop from high to low of the output trigger is tied to threshold.

Figure 1 : Minimum Pulse Width Required for Trigering

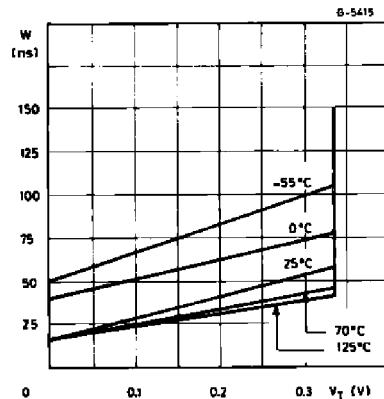


Figure 2 : Supply Current versus Supply Voltage

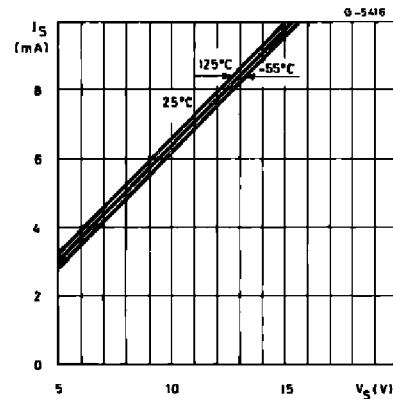


Figure 3 : Delay Time versus Temperature

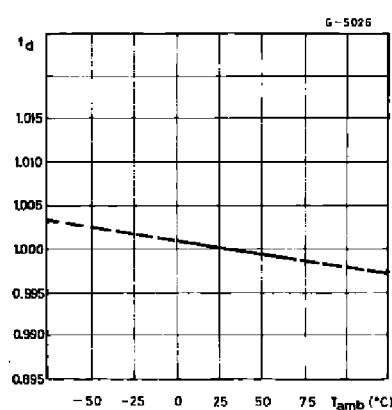


Figure 4 : Low Output Voltage versus Output Sink Current

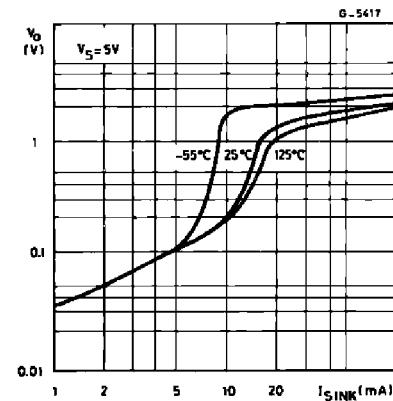


Figure 5 : Low Output Voltage versus Output Sink Current

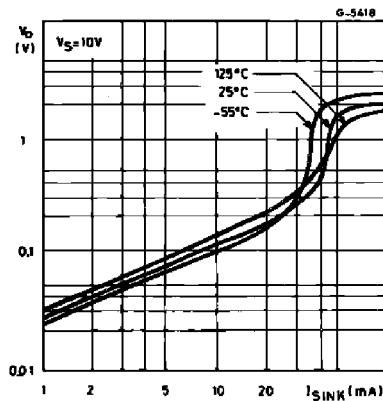


Figure 6 : Low Output Voltage versus Output Sink Current

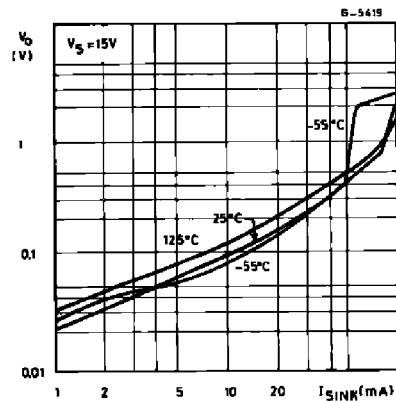


Figure 7 : High Output Voltage Drop versus Output

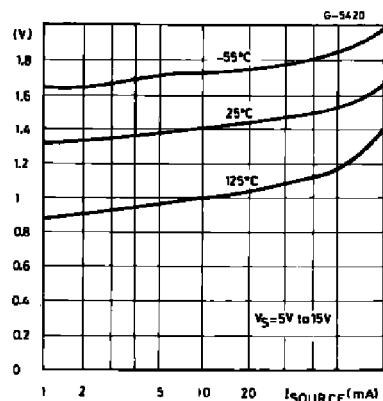


Figure 8 : Delay Time versus Supply Voltage

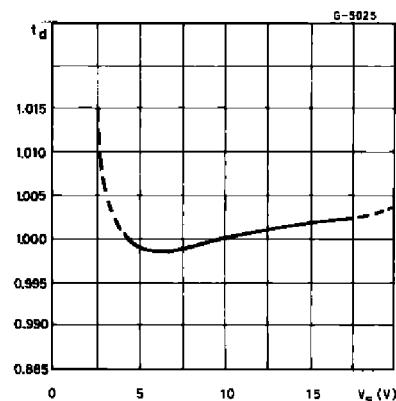
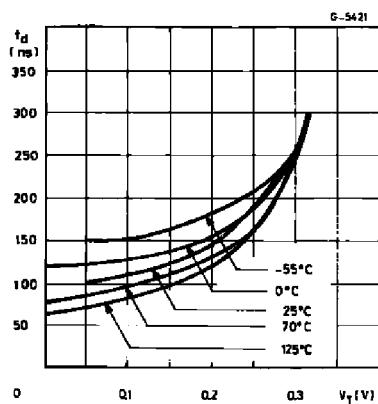


Figure 9 : Propagation Delay versus Voltage Level of Trigger Value

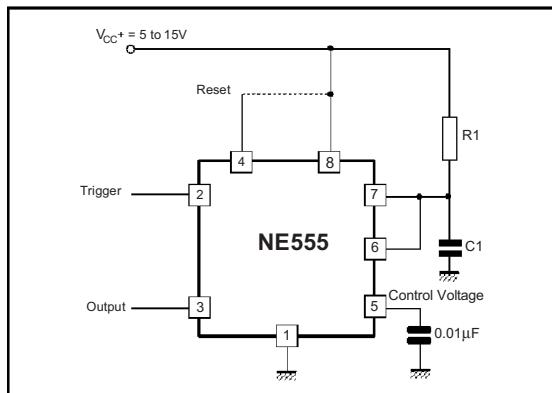


APPLICATION INFORMATION

MONOSTABLE OPERATION

In the monostable mode, the timer functions as a one-shot. Referring to figure 10 the external capacitor is initially held discharged by a transistor inside the timer.

Figure 10



The circuit triggers on a negative-going input signal when the level reaches $1/3 V_{cc}$. Once triggered, the circuit remains in this state until the set time has elapsed, even if it is triggered again during this interval. The duration of the output HIGH state is given by $t = 1.1 R_1 C_1$ and is easily determined by figure 12.

Notice that since the charge rate and the threshold level of the comparator are both directly proportional to supply voltage, the timing interval is independent of supply. Applying a negative pulse simultaneously to the reset terminal (pin 4) and the trigger terminal (pin 2) during the timing cycle discharges the external capacitor and causes the cycle to start over. The timing cycle now starts on the positive edge of the reset pulse. During the time the reset pulse is applied, the output is driven to its LOW state.

When a negative trigger pulse is applied to pin 2, the flip-flop is set, releasing the short circuit across the external capacitor and driving the output HIGH. The voltage across the capacitor increases exponentially with the time constant $\tau = R_1 C_1$. When the voltage across the capacitor equals $2/3 V_{cc}$, the comparator resets the flip-flop which then discharges the capacitor rapidly and drives the output to its LOW state.

Figure 11 shows the actual waveforms generated in this mode of operation.

When Reset is not used, it should be tied high to avoid any possibly or false triggering.

Figure 11

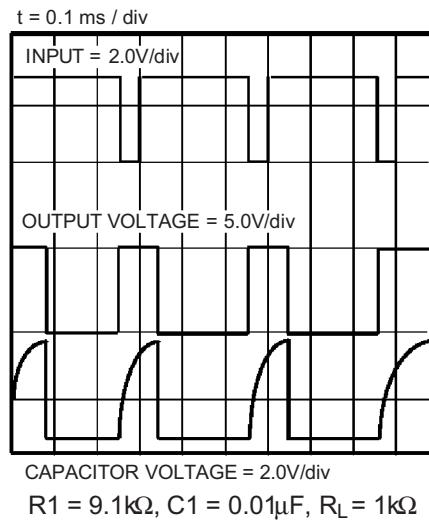
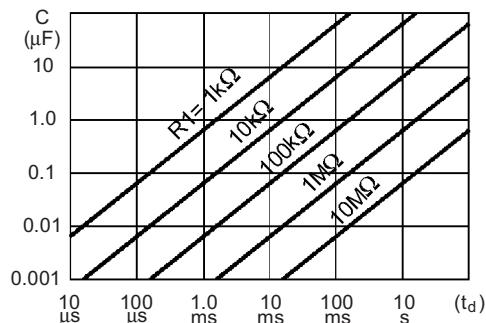


Figure 12



ASTABLE OPERATION

When the circuit is connected as shown in figure 13 (pin 2 and 6 connected) it triggers itself and free runs as a multivibrator. The external capacitor charges through R_1 and R_2 and discharges through R_2 only. Thus the duty cycle may be precisely set by the ratio of these two resistors.

In the astable mode of operation, C_1 charges and discharges between $1/3 V_{cc}$ and $2/3 V_{cc}$. As in the triggered mode, the charge and discharge times and therefore frequency are independent of the supply voltage.

Figure 13

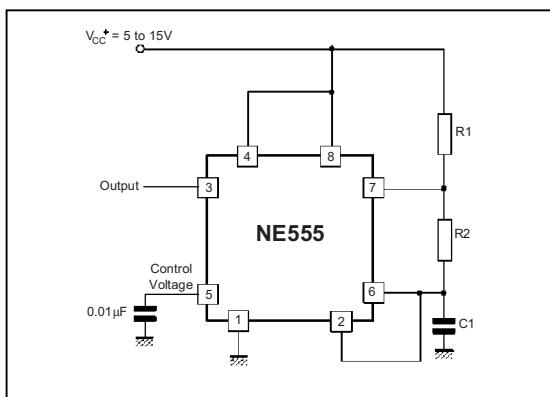


Figure 14 shows actual waveforms generated in this mode of operation.

The charge time (output HIGH) is given by :

$$t_1 = 0.693 (R_1 + R_2) C_1$$

and the discharge time (output LOW) by :

$$t_2 = 0.693 (R_2) C_1$$

Thus the total period T is given by :

$$T = t_1 + t_2 = 0.693 (R_1 + 2R_2) C_1$$

The frequency of oscillation is then :

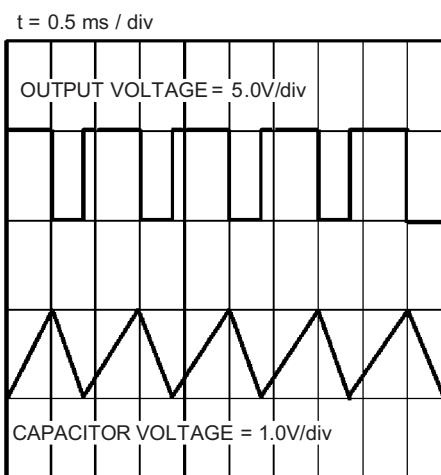
$$f = \frac{1}{T} = \frac{1.44}{(R_1 + 2R_2) C_1}$$

and may be easily found by figure 15.

The duty cycle is given by :

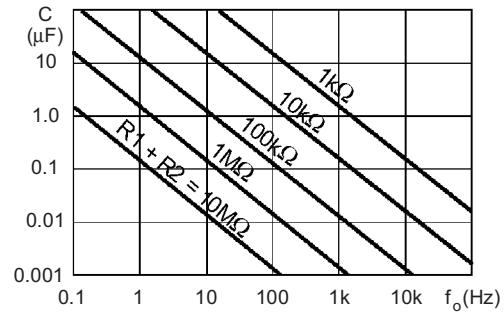
$$D = \frac{R_2}{R_1 + 2R_2}$$

Figure 14



$$R_1 = R_2 = 4.8\text{k}\Omega, C_1 = 0.1\mu\text{F}, R_L = 1\text{k}\Omega$$

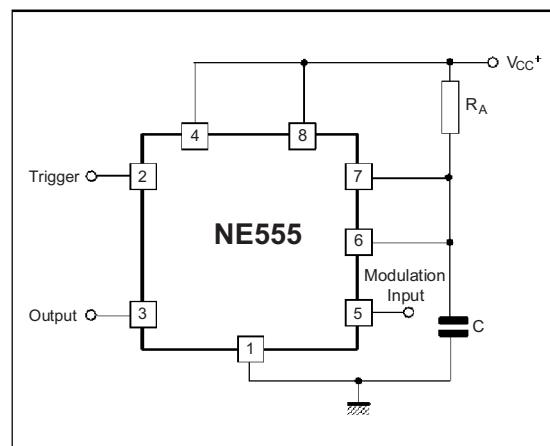
Figure 15 : Free Running Frequency versus R₁, R₂ and C₁



PULSE WIDTH MODULATOR

When the timer is connected in the monostable mode and triggered with a continuous pulse train, the output pulse width can be modulated by a signal applied to pin 5. Figure 16 shows the circuit.

Figure 16 : Pulse Width Modulator.



NE555/SA555/SE555

LINEAR RAMP

When the pullup resistor, R_A , in the monostable circuit is replaced by a constant current source, a linear ramp is generated. Figure 17 shows a circuit configuration that will perform this function.

Figure 17.

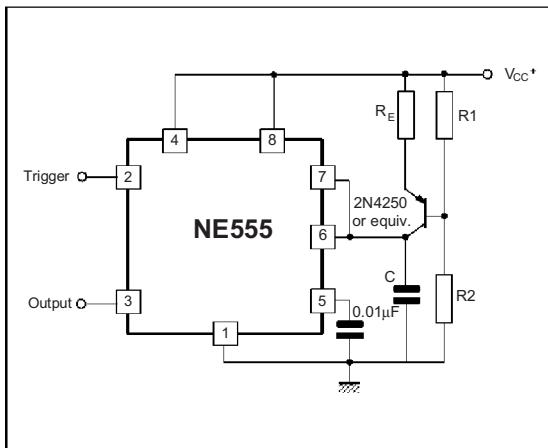
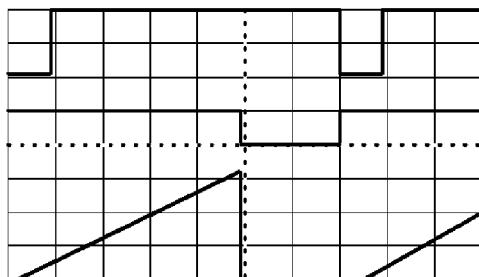


Figure 18 shows waveforms generator by the linear ramp.

The time interval is given by :

$$T = \frac{(2/3 V_{CC} R_E (R_1 + R_2) C)}{R_1 V_{CC} - V_{BE} (R_1 + R_2)} V_{BE} = 0.6V$$

Figure 18 : Linear Ramp.



$V_{CC} = 5V$
 Time = $20\mu s/DIV$
 $R_1 = 47k\Omega$
 $R_2 = 100k\Omega$
 $R_E = 2.7k\Omega$
 $C = 0.01\mu F$

Top trace : input 3V/DIV
 Middle trace : output 5V/DIV
 Bottom trace : output 5V/DIV
 Bottom trace : capacitor voltage 1V/DIV

50% DUTY CYCLE OSCILLATOR

For a 50% duty cycle the resistors R_A and R_E may be connected as in figure 19. The time period for the output high is the same as previous, $t_1 = 0.693 R_A C$.

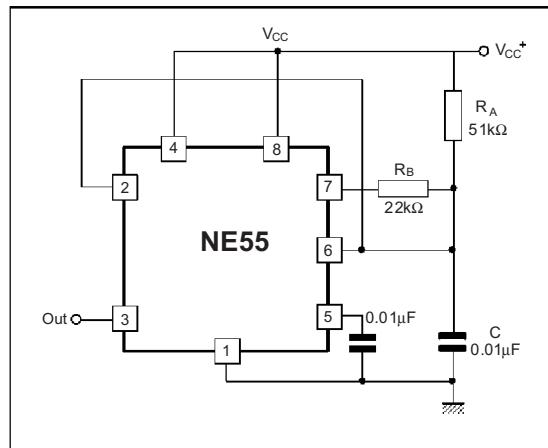
For the output low it is $t_2 =$

$$[(R_A R_B)/(R_A + R_B)] C \ln \left[\frac{R_B - 2R_A}{2R_B - R_A} \right]$$

$$\text{Thus the frequency of oscillation is } f = \frac{1}{t_1 + t_2}$$

Note that this circuit will not oscillate if R_B is greater

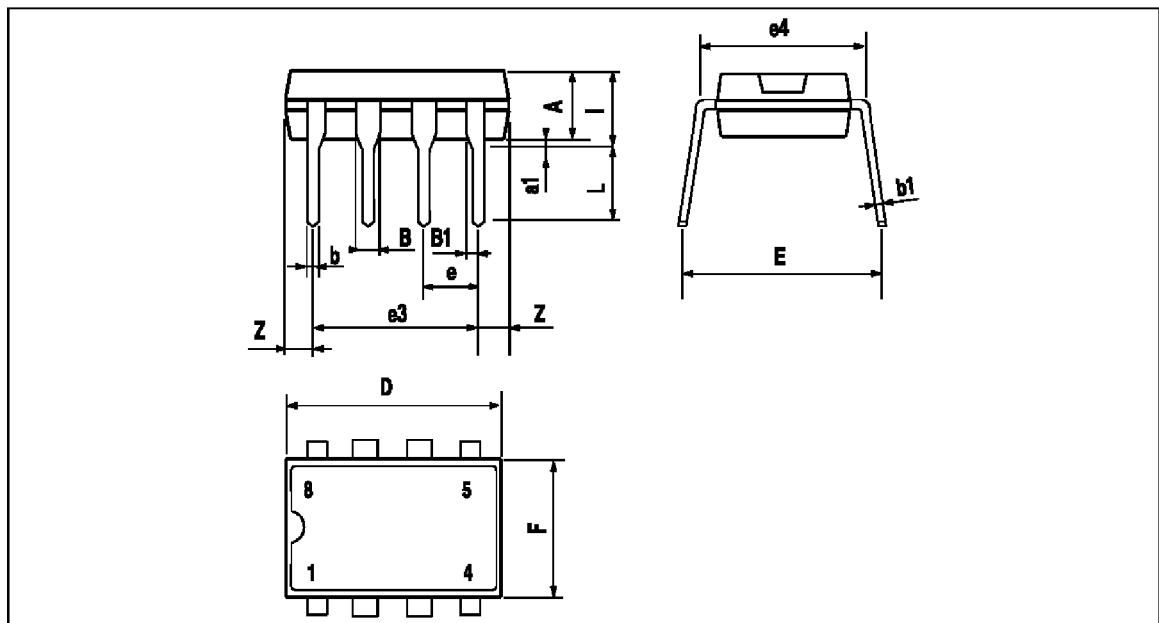
Figure 19 : 50% Duty Cycle Oscillator.



than $1/2 R_A$ because the junction of R_A and R_B cannot bring pin 2 down to $1/3 V_{CC}$ and trigger the lower comparator.

ADDITIONAL INFORMATION

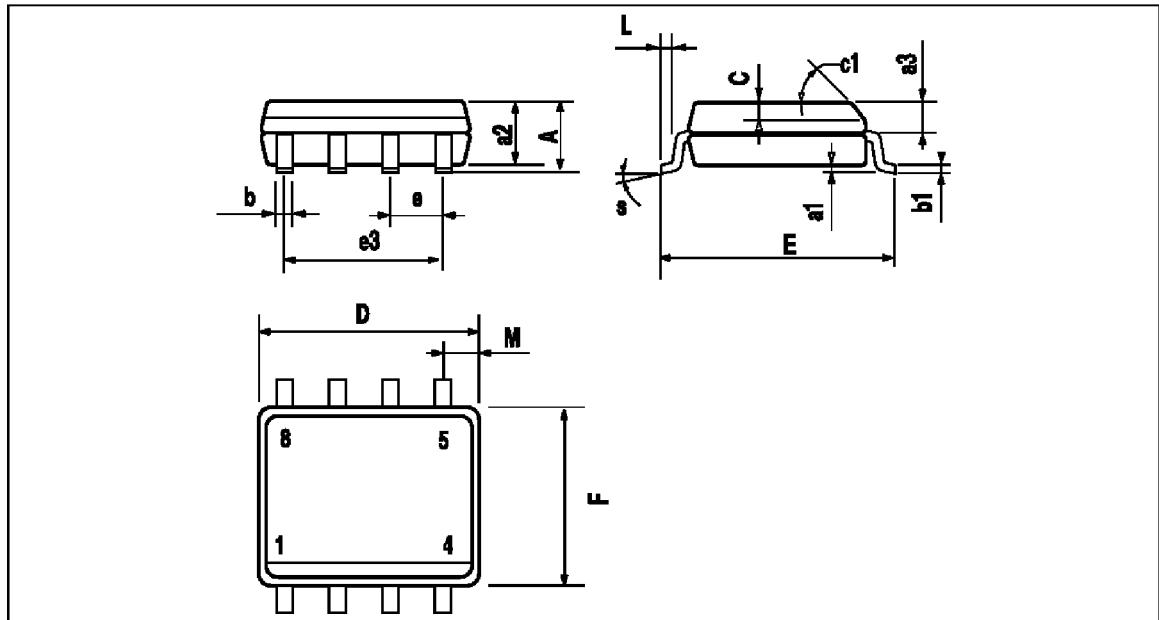
Adequate power supply bypassing is necessary to protect associated circuitry. Minimum recommended is $0.1\mu F$ in parallel with $1\mu F$ electrolytic.

PACKAGE MECHANICAL DATA
 8 PINS - PLASTIC DIP


PM-DIP8.EPS

DIP8.TBL

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
i			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

PACKAGE MECHANICAL DATA
 8 PINS - PLASTIC MICROPACKAGE (SO)


PM-SO8-EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.020
c1		45° (typ.)				
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S		8° (max.)				

SO8-TBL

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ORDER CODE :



DATA SHEET

Logic

Order code	Manufacturer code	Description
83-0420	HCF4093BEY	4093B QUAD 2 INPUT NAND SCHMITT TRIG RC

Logic

Page 1 of 14

The enclosed information is believed to be correct. Information may change 'without notice' due to product improvement. Users should ensure that the product is suitable for their use. E. & O. E.

Revision A
20/02/2007

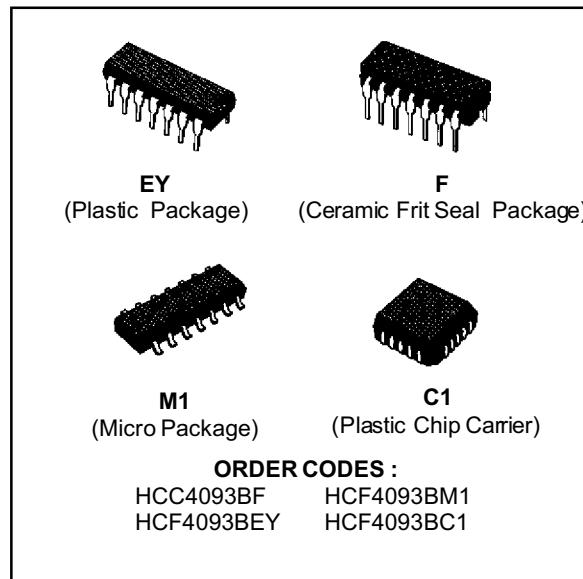
Sales: 01206 751166
Sales@rapidelec.co.uk

Technical: 01206 835555
Tech@rapidelec.co.uk

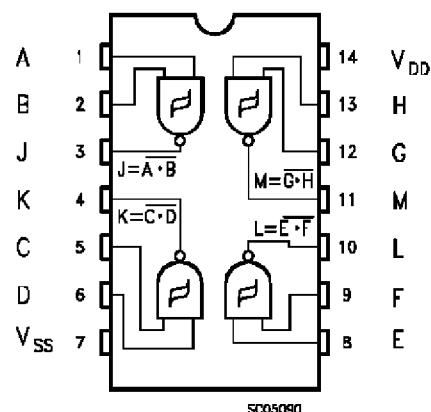
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QUAD 2-INPUT NAND SCHMIDT TRIGGERS

- SCHMITT-TRIGGER ACTION ON EACH INPUT WITH NO EXTERNAL COMPONENTS
- HYSTERESIS VOLTAGE TYPICALLY 0.9V AT $V_{DD} = 5V$ AND 2.3V AT $V_{DD} = 10V$
- NOISE IMMUNITY GREATER THAN 50% OF V_{DD} (typ.)
- NO LIMIT ON INPUT RISE AND FALL TIMES
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TEMPORARY STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



PIN CONNECTIONS



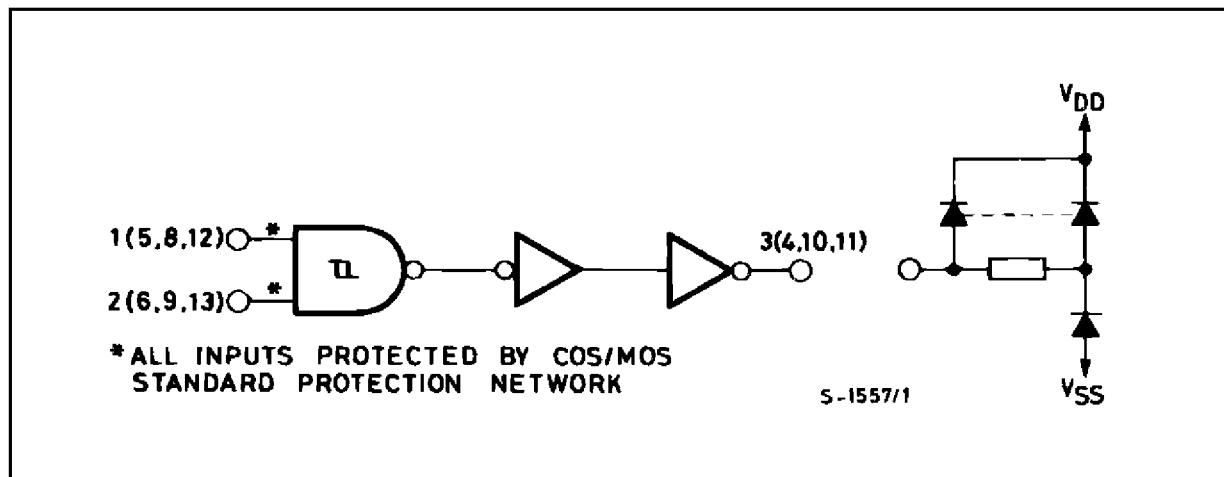
DESCRIPTION

The HCC4093B (extended temperature range) and HCF4093B (intermediate temperature range) are available in 14-lead dual in-line plastic or ceramic package and plastic micropackage. The HCC/HCF4093B consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive and negative-going signals.

The difference between the positive voltage (V_P) and the negative voltage (V_N) is defined as hysteresis voltage (V_H) (see fig. 1).

FUNCTIONAL DIAGRAM

1 of 4 Schmitt triggers



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	– 0.5 to + 20 – 0.5 to + 18	V V
V _I	Input Voltage	– 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C
T _{stg}	Storage Temperature	– 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V_I (V)	V_o (V)	$ I_{O1} $ (μ A)	V_{DD} (V)	T_{Low}^*		$25^\circ C$			T_{High}^*		
						Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I_L	Quiescent Current HCC Types	0/ 5			5		1		0.02	1		30	μ A
		0/10			10		2		0.02	2		60	
		0/15			15		4		0.02	4		120	
		0/20			20		20		0.04	20		600	
	HCF Types	0/ 5			5		4		0.02	4		30	
		0/10			10		8		0.02	8		60	
		0/15			15		16		0.02	16		120	
		a			5	2.2	3.6	2.2	2.9	3.6	2.2	3.6	
V_P	Positive Trigger Threshold Voltage	a			10	4.6	7.1	4.6	5.9	7.1	4.6	7.1	V
		a			15	6.8	10.8	6.8	8.8	10.8	6.8	10.8	
		b			5	2.6	4	2.6	3.3	4	2.6	4	
		b			10	5.6	8.2	5.6	7	8.2	5.6	8.2	
		b			15	6.3	12.7	6.3	9.4	12.7	6.3	12.7	
		a			5	0.9	2.8	0.9	1.9	2.8	0.9	2.8	
V_N	Negative Trigger Threshold Voltage	a			10	2.5	5.2	2.5	3.9	5.2	2.5	5.2	V
		a			15	4	7.4	4	5.8	7.4	4	7.4	
		b			5	1.4	3.2	1.4	2.3	3.2	1.4	3.2	
		b			10	3.4	6.6	3.4	5.1	6.6	3.4	6.6	
		b			15	4.8	9.6	4.8	7.3	9.6	4.8	9.6	
		a			5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	
V_H	Hysteresis Voltage	a			10	1.2	3.4	1.2	2.3	3.4	1.2	3.4	V
		a			15	1.6	5	1.6	3.5	5	1.6	5	
		b			5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	
		b			10	1.2	3.4	1.2	2.3	3.4	1.2	3.4	
		b			15	1.6	5	1.6	3.5	5	1.6	5	
		a			5	4.95		4.95			4.95		
V_{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95				4.95		V
		0/10	< 1	10	9.95		9.95				9.95		
		0/15	< 1	15	14.95		14.95				14.95		
V_{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05		V
		10/0	< 1	10		0.05			0.05		0.05		
		15/0	< 1	15		0.05			0.05		0.05		
		a			5	- 2		- 1.6	- 3.2		- 1.15		
I_{OH}	Output Drive Current HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15		mA
		0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
		0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
		0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
		0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
		0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		
	HCF Types	0/ 5	2.5		5								
		0/ 5	4.6		5								

a : input on terminals 1, 5, 8, 12 or 2, 6, 9, 13 ; other inputs to V_{DD} .b : input on terminals 1 and 2, 5 and 6, 8 and 9, or 12 and 13 ; other inputs to V_{DD} .* T_{Low} = $-55^\circ C$ for HCC device : $-40^\circ C$ for HCF device.* T_{High} = $+125^\circ C$ for HCC device : $+85^\circ C$ for HCF device.

STATIC ELECTRICAL CHARACTERISTICS (continued)

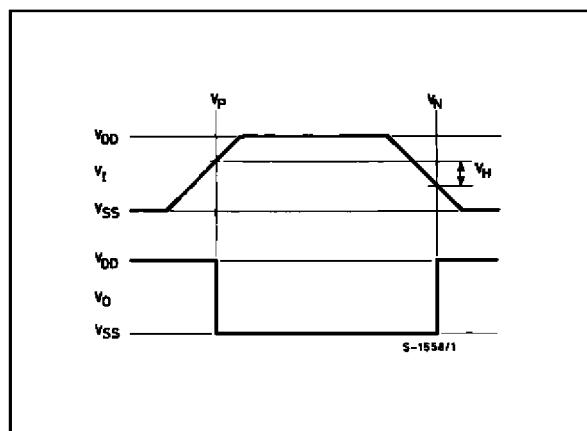
Symbol	Parameter	Test Conditions				Value						Unit	
		V_I (V)	V_o (V)	$ I_{OL} $ (μA)	V_{DD} (V)	T_{Low}^*		$25^\circ C$			T_{High}^*		
						Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I_{OL}	Output Sink Current	0/ 5	0.4		5	0.64		0.51	1		0.36		mA
		0/10	0.5		10	1.6		1.3	2.6		0.9		
		0/15	1.5		15	4.2		3.4	6.8		2.4		
		0/ 5	0.4		5	0.52		0.44	1		0.36		
		0/10	0.5		10	1.3		1.1	2.6		0.9		
		0/15	1.5		15	3.6		3.0	6.8		2.4		
I_{IH}, I_{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μA
			0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C_I	Input Capacitance		Any Input						5	7.5			pF

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^\circ C$, $C_L = 50pF$, $R_L = 200k\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/{^\circ C}$ values , all input rise and fall time = 20ns)

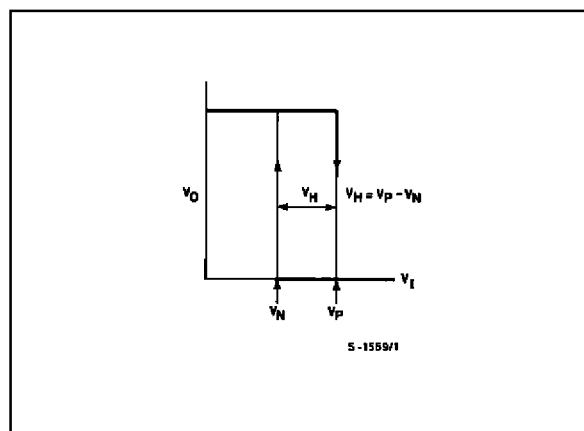
Symbol	Parameter	Test Conditions			Value			Unit
		V_{DD} (V)	Min.	Typ.	Max.			
t_{PLH}, t_{PHL}	Propagation Delay Time		5		190	380	ns	
			10		90	180		
			15		65	130		
t_{TLH}, t_{THL}	Transition Time		5		100	200	ns	
			10		50	100		
			15		40	80		

Figure1 : Hysteresis Definition, Characteristics and Test Setup.

(a) Definition of V_P , V_N and V_H



(b) Transfer characteristics of 1 of 4 gates



(c) Test setup

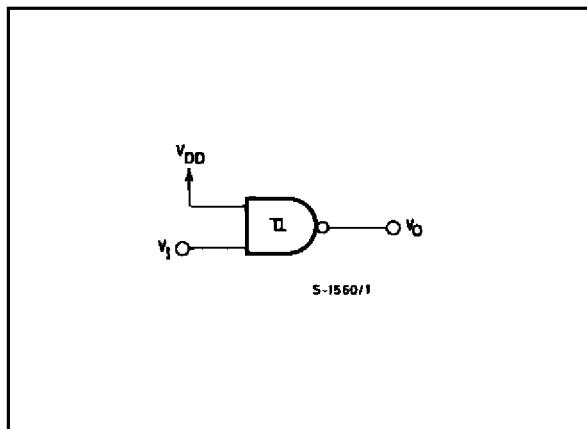


Figure 2 : Input and Output Characteristics.

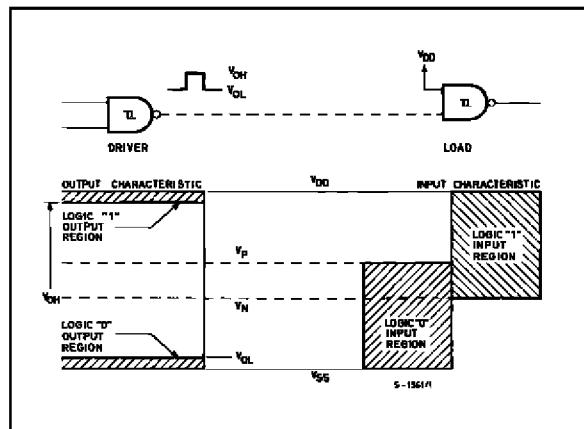


Figure 3 : Typical Current and Voltage Transfer Characteristics.

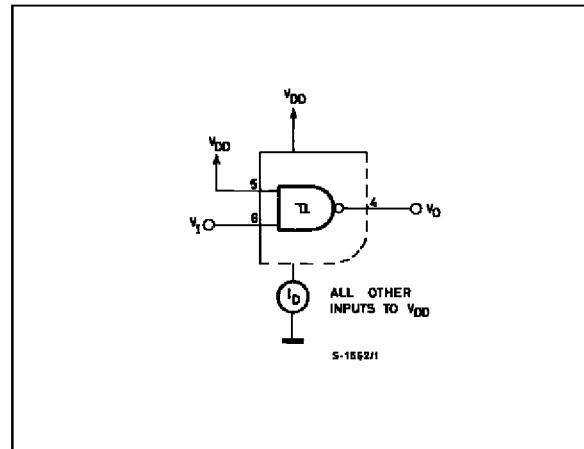
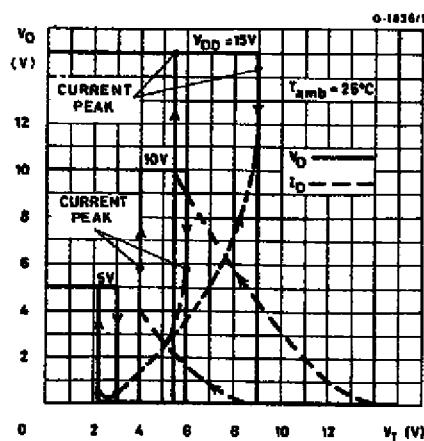
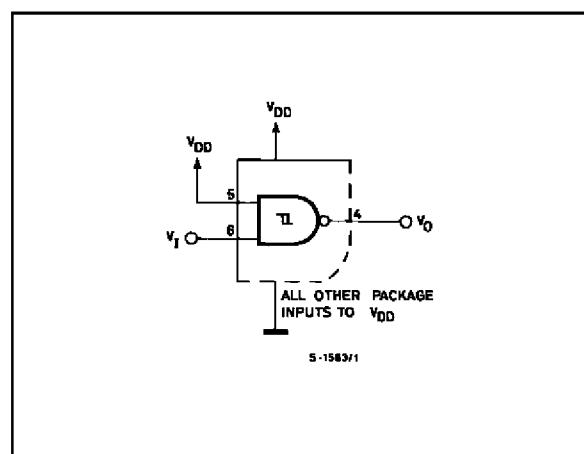
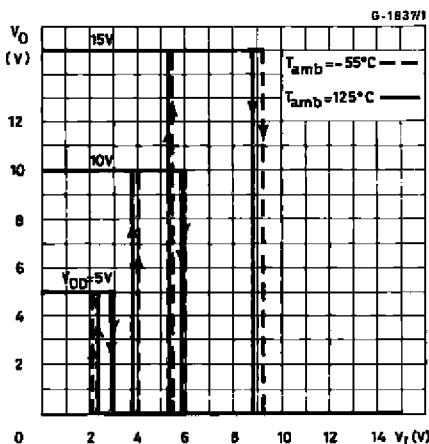


Figure 4 : Typical Voltage Transfer Characteristics as a Function of Temperature, and Test Circuit.



HCC/HCF4093B

Figure 5 : Typical Output Low (sink) Current Characteristics.

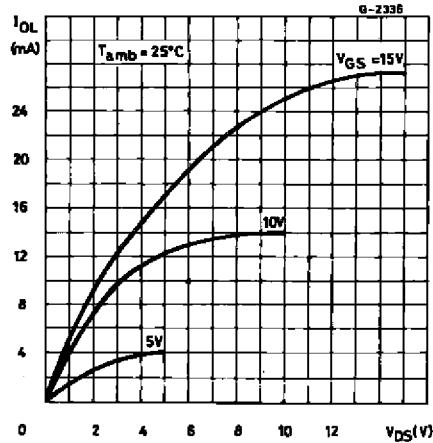


Figure 7 : Typical Output High (source) Current Characteristic.

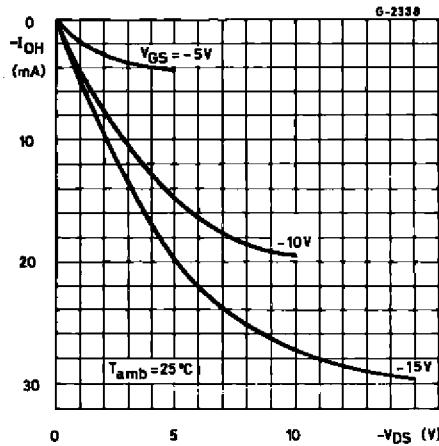


Figure 9 : Typical Propagation Delay Time vs. Supply Voltage.

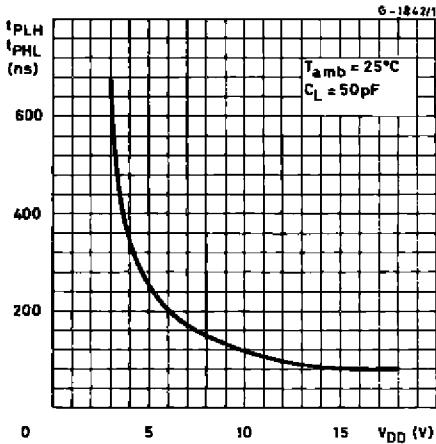


Figure 6 : Minimum Output Low (sink) Current Characteristics.

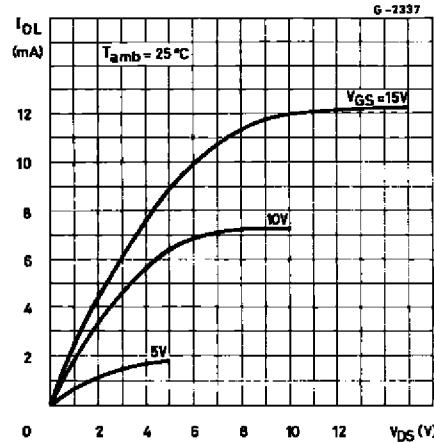


Figure 8 : Minimum Output High Current Characteristics.

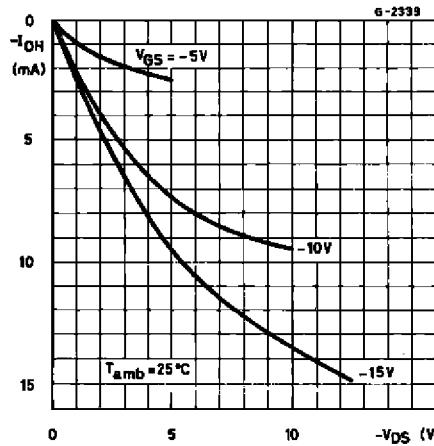


Figure 10 : Typical Transition Time vs. Load Capacitance.

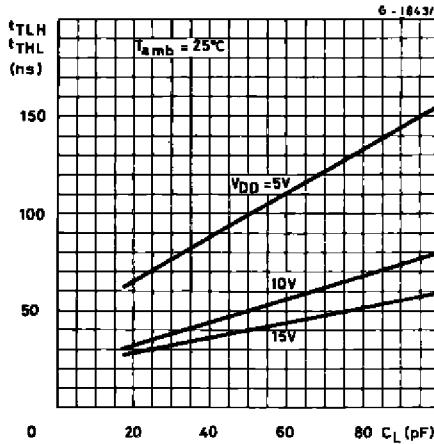


Figure 11 : Typical Trigger Threshold Voltage vs. V_{DD}

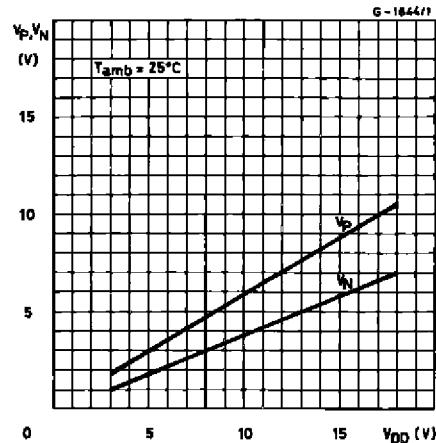


Figure 13 : Typical Dissipation Characteristics.

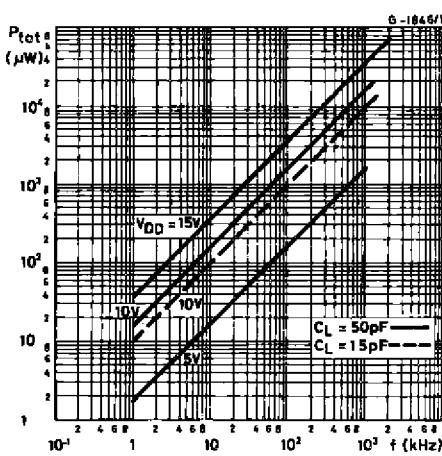


Figure 12 : Typical per cent Hysteresis vs. Supply Voltage.

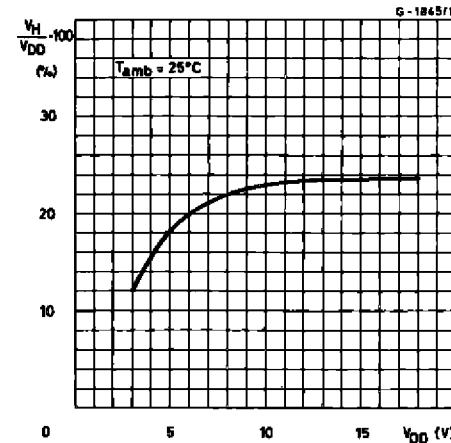
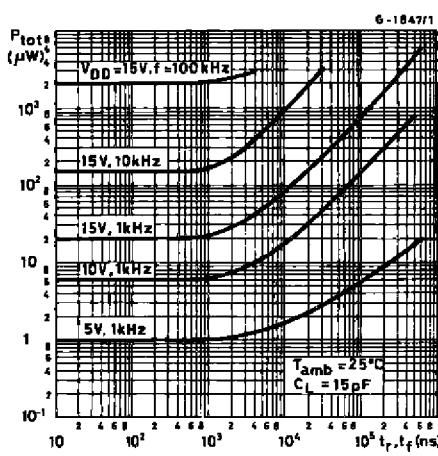


Figure 14 : Power Dissipation vs. Rise and Fall Times.



APPLICATIONS

Figure 15 : Wave Shaper.

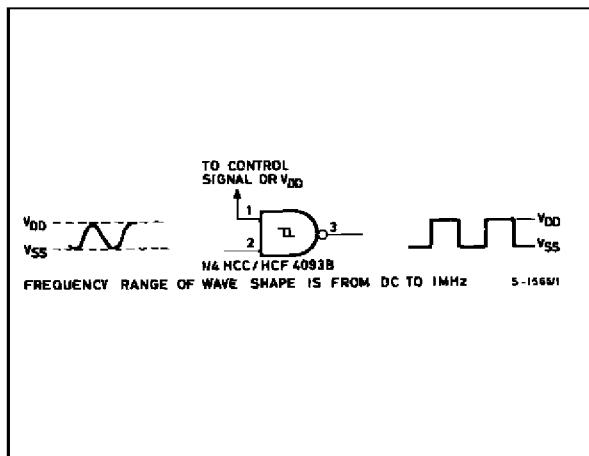


Figure 16 : Monostable Multivibrator.

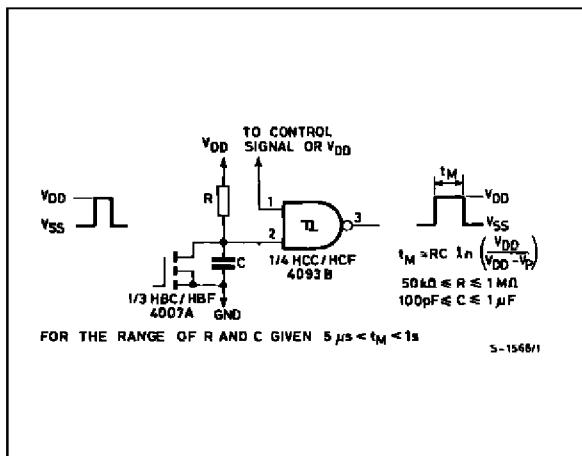
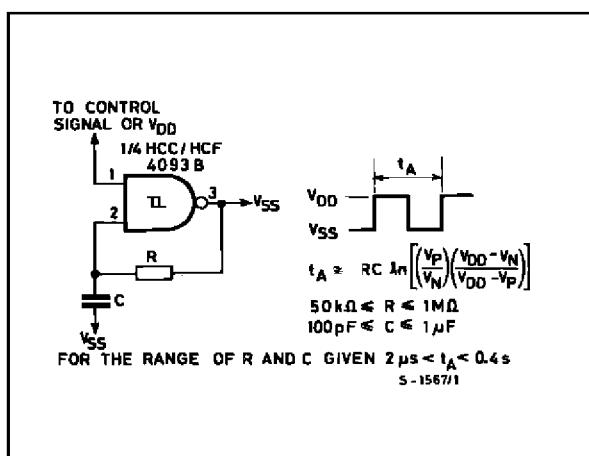


Figure 17 : Astable Multivibrator.



TEST CIRCUITS

Figure 18 : Quiescent Device Current.

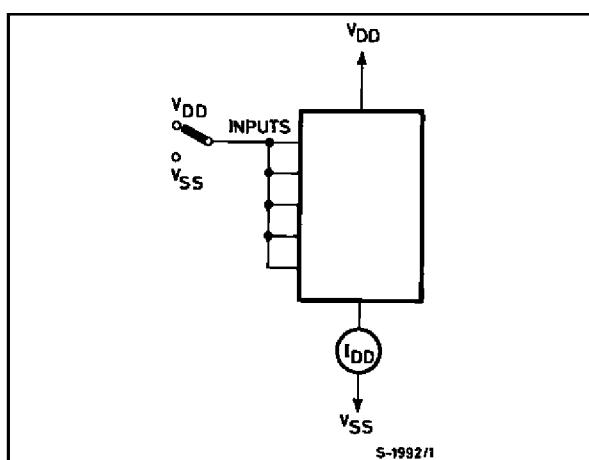
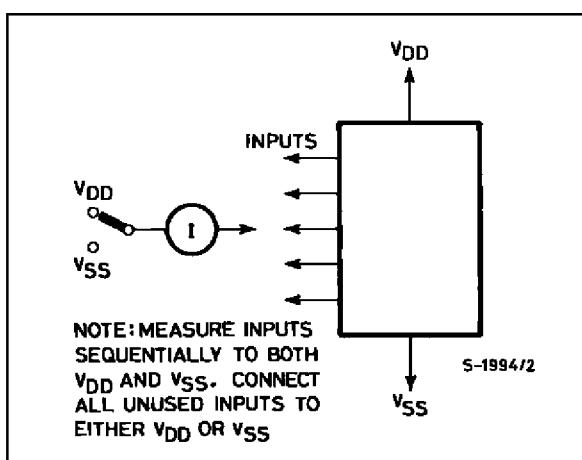
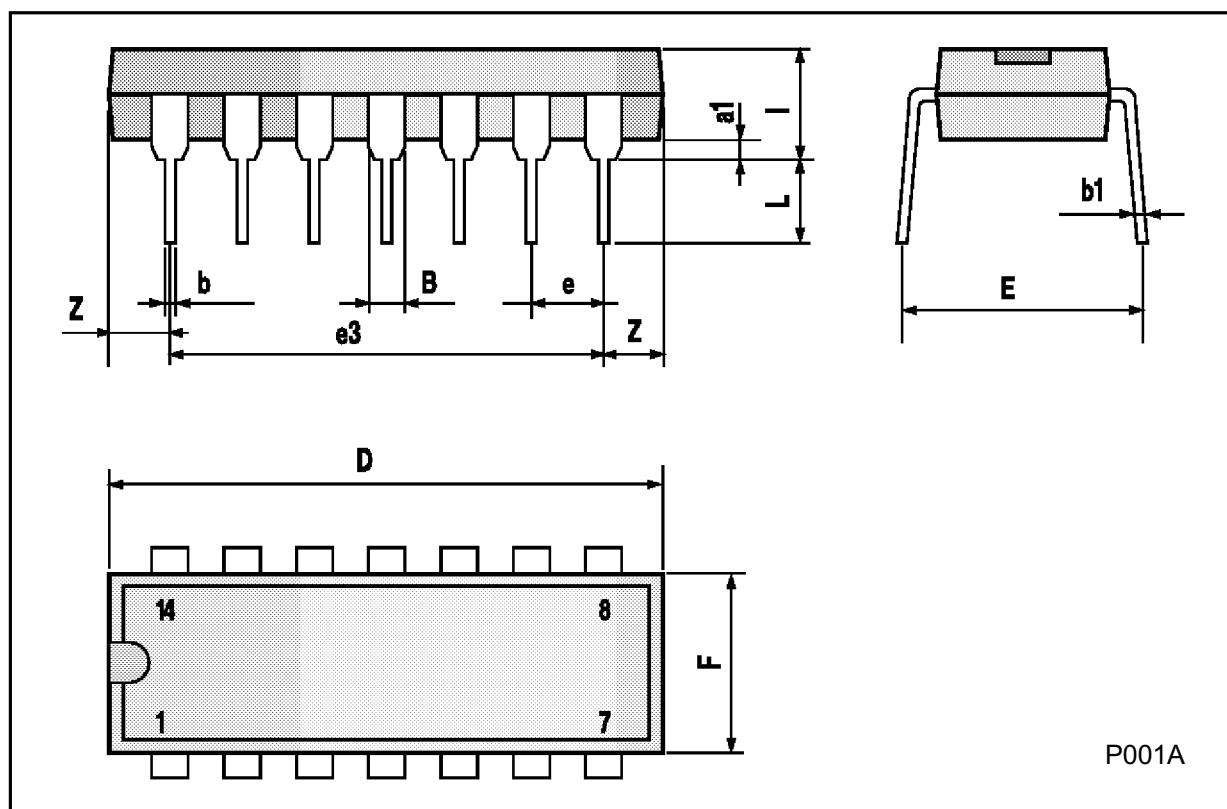


Figure 19 : Input Leakage Current.



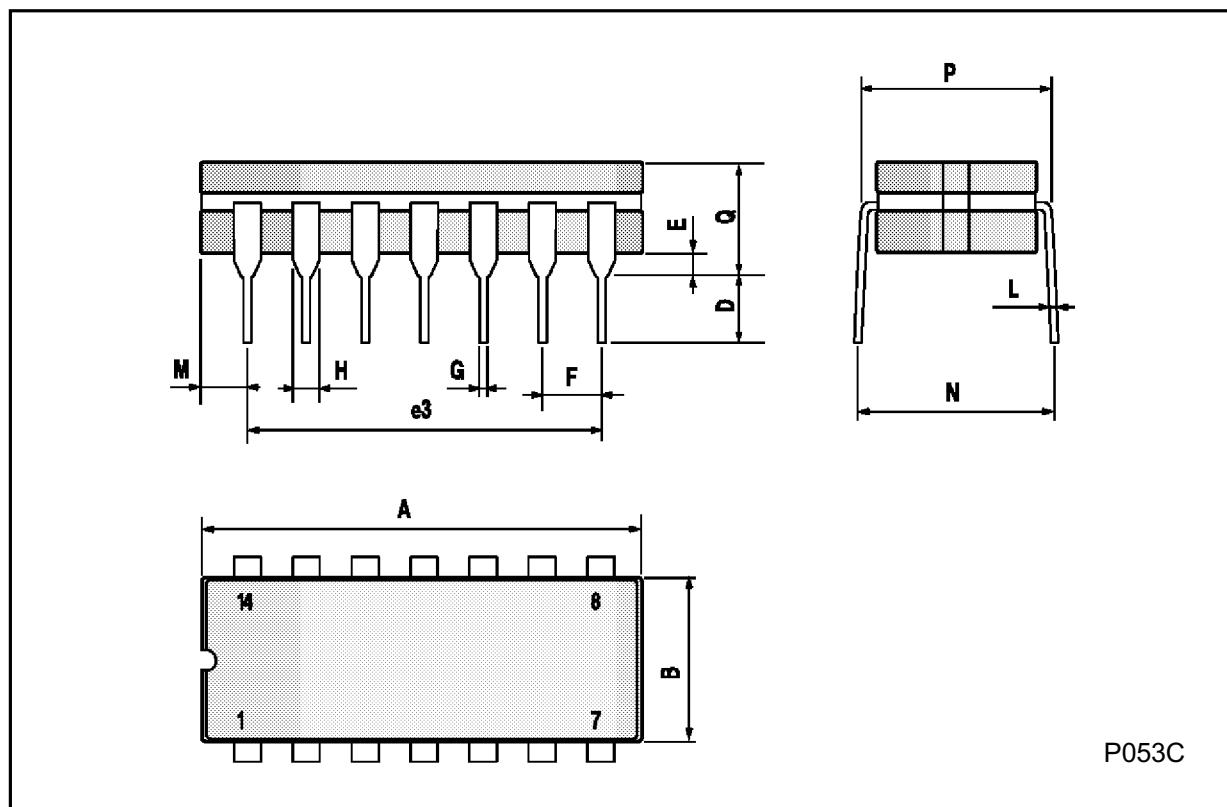
Plastic DIP14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



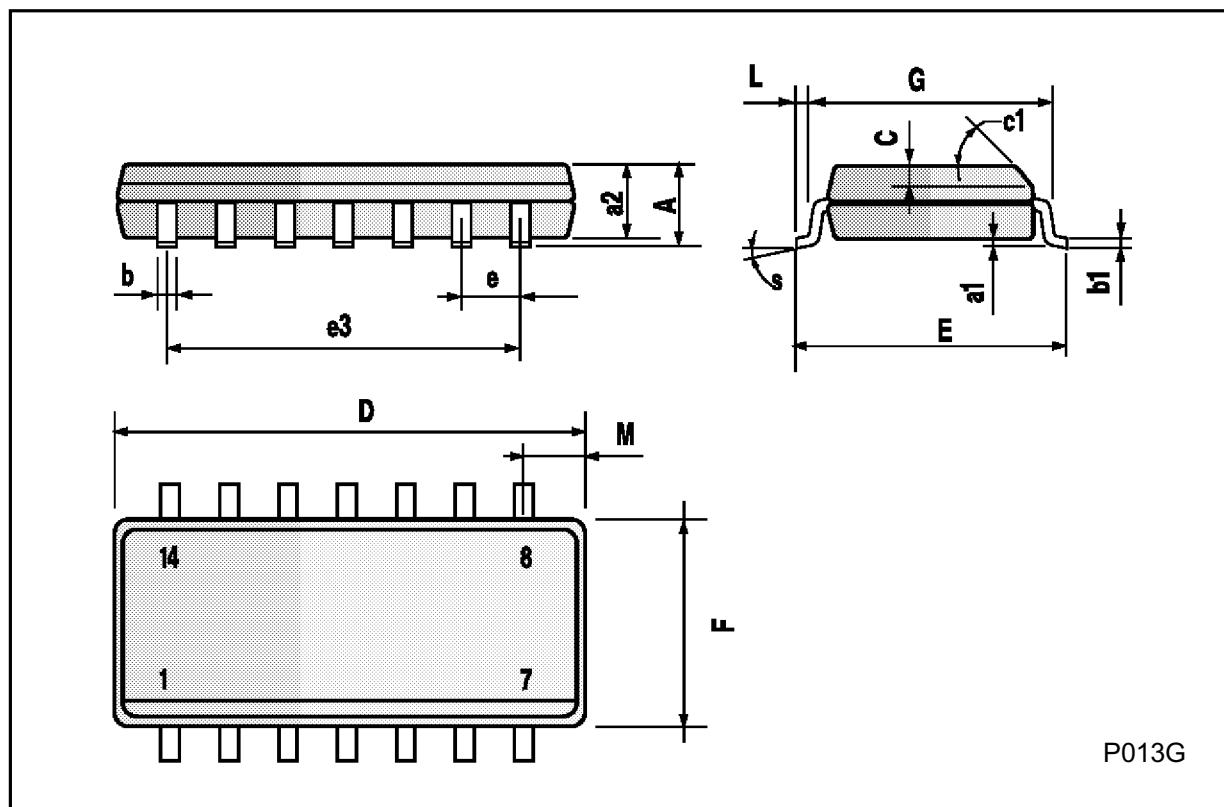
Ceramic DIP14/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



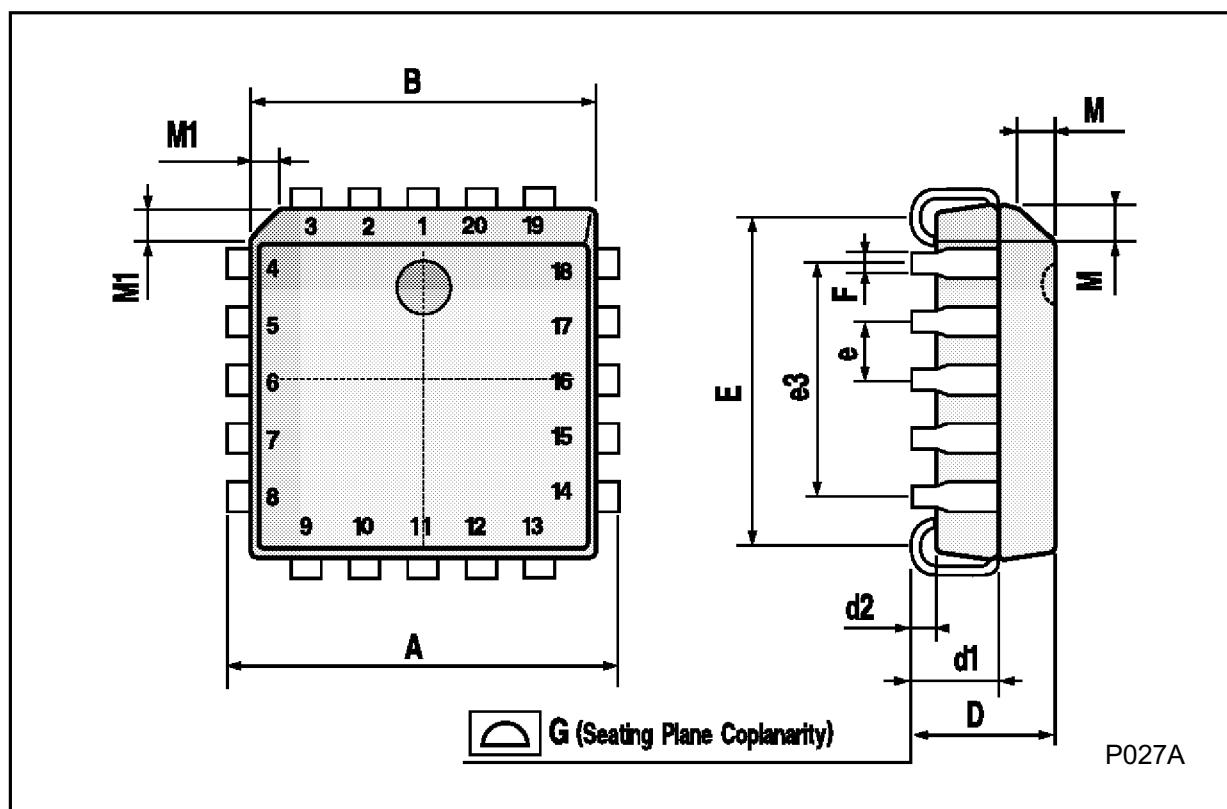
SO14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1			45° (typ.)			
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S			8° (max.)			



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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